

# IRF5803

HEXFET<sup>®</sup> Power MOSFET

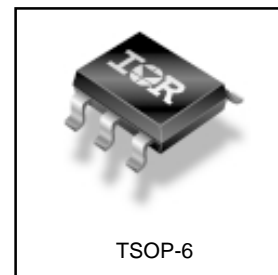
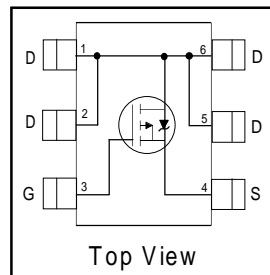
- Ultra Low On-Resistance
- P-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- Low Gate Charge

V <sub>DSS</sub>	R <sub>DS(on)</sub> max (mΩ)	I <sub>D</sub>
<b>-40V</b>	112@V <sub>GS</sub> = -10V	-3.4A
	190@V <sub>GS</sub> = -4.5V	-2.7A

## Description

These P-channel HEXFET<sup>®</sup> Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve the extremely low on-resistance per silicon area. This benefit provides the designer with an extremely efficient device for use in battery and load management applications.

The TSOP-6 package with its customized leadframe produces a HEXFET<sup>®</sup> power MOSFET with R<sub>DS(on)</sub> 60% less than a similar size SOT-23. This package is ideal for applications where printed circuit board space is at a premium. It's unique thermal design and R<sub>DS(on)</sub> reduction enables a current-handling increase of nearly 300% compared to the SOT-23.



## Absolute Maximum Ratings

	Parameter	Max.	Units
V <sub>DS</sub>	Drain- Source Voltage	-40	V
I <sub>D</sub> @ T <sub>A</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ -10V	-3.4	A
I <sub>D</sub> @ T <sub>A</sub> = 70°C	Continuous Drain Current, V <sub>GS</sub> @ -10V	-2.7	
I <sub>DM</sub>	Pulsed Drain Current ①	-27	
P <sub>D</sub> @ T <sub>A</sub> = 25°C	Power Dissipation ③	2.0	W
P <sub>D</sub> @ T <sub>A</sub> = 70°C	Power Dissipation ③	1.3	
	Linear Derating Factor	16	mW/°C
V <sub>GS</sub>	Gate-to-Source Voltage	± 20	V
T <sub>J</sub> , T <sub>STG</sub>	Junction and Storage Temperature Range	-55 to + 150	°C

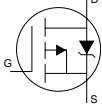
## Thermal Resistance

	Parameter	Max.	Units
R <sub>θJA</sub>	Maximum Junction-to-Ambient ③	62.5	°C/W

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

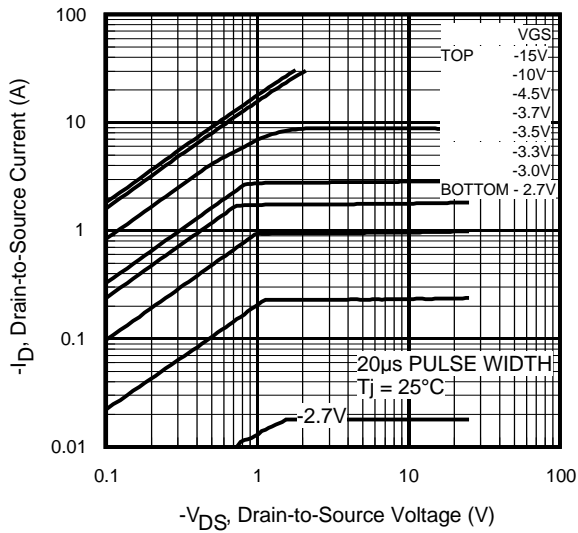
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-40	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.03	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}$ , $I_D = -1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	112	m $\Omega$	$V_{GS} = -10V, I_D = -3.4$ ②
		—	—	190		$V_{GS} = -4.5V, I_D = -2.7A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	—	-3.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
$g_{fs}$	Forward Transconductance	4.0	—	—	S	$V_{DS} = -10V, I_D = -3.4A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	-10	$\mu A$	$V_{DS} = -32V, V_{GS} = 0V$
		—	—	-25		$V_{DS} = -32V, V_{GS} = 0V, T_J = 70^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$
$Q_g$	Total Gate Charge	—	25	37	nC	$I_D = -3.4A$
$Q_{gs}$	Gate-to-Source Charge	—	4.5	6.8		$V_{DS} = -20V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	3.5	5.3		$V_{GS} = -10V$
$t_{d(on)}$	Turn-On Delay Time	—	43	—	ns	$V_{DD} = -20V$ ②
$t_r$	Rise Time	—	550	—		$I_D = -1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	88	—		$R_G = 6.0\Omega$
$t_f$	Fall Time	—	50	—		$V_{GS} = -10V$
$C_{iss}$	Input Capacitance	—	1110	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	93	—		$V_{DS} = -25V$
$C_{rss}$	Reverse Transfer Capacitance	—	73	—		$f = 100\text{kHz}$

## Source-Drain Ratings and Characteristics

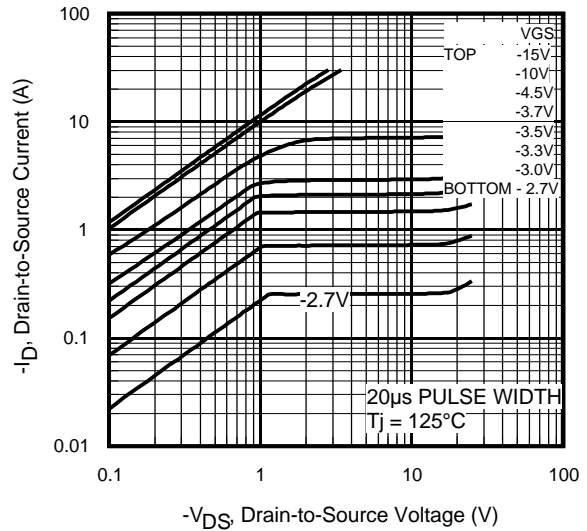
	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	-2.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	-27		
$V_{SD}$	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}, I_S = -2.0A, V_{GS} = 0V$ ②
$t_{rr}$	Reverse Recovery Time	—	27	40	ns	$T_J = 25^\circ\text{C}, I_F = -2.0A$
$Q_{rr}$	Reverse Recovery Charge	—	34	50	nC	$di/dt = -100A/\mu s$ ②

### Notes:

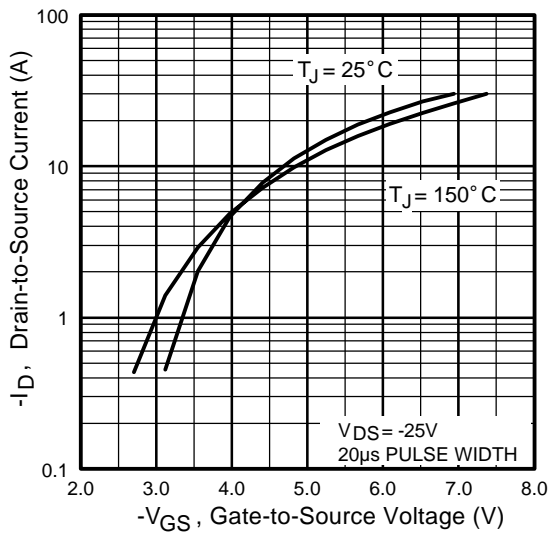
- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width  $\leq 400\mu s$ ; duty cycle  $\leq 2\%$ .
- ③ Surface mounted on 1 in square Cu board



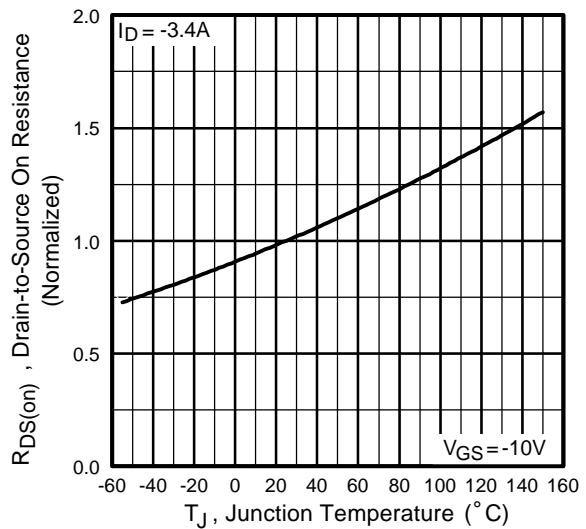
**Fig 1.** Typical Output Characteristics



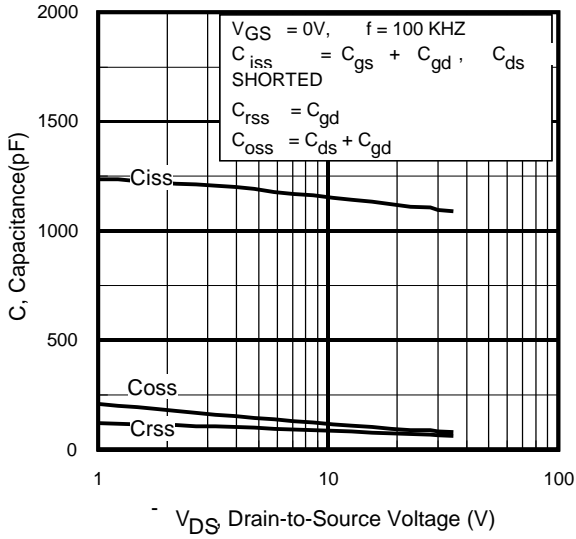
**Fig 2.** Typical Output Characteristics



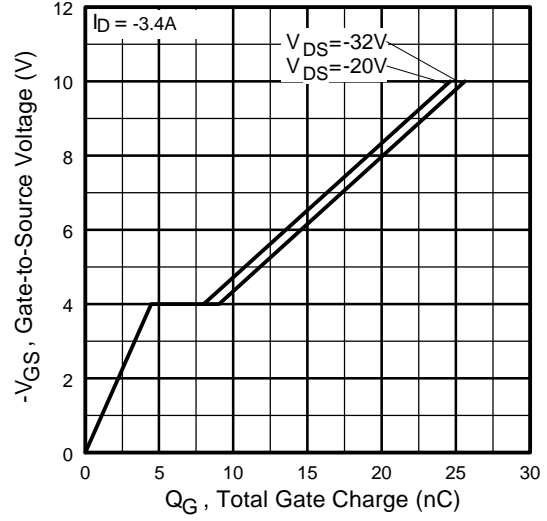
**Fig 3.** Typical Transfer Characteristics



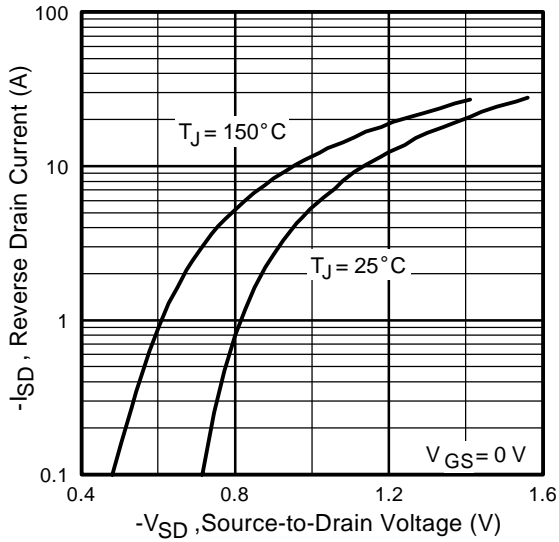
**Fig 4.** Normalized On-Resistance Vs. Temperature



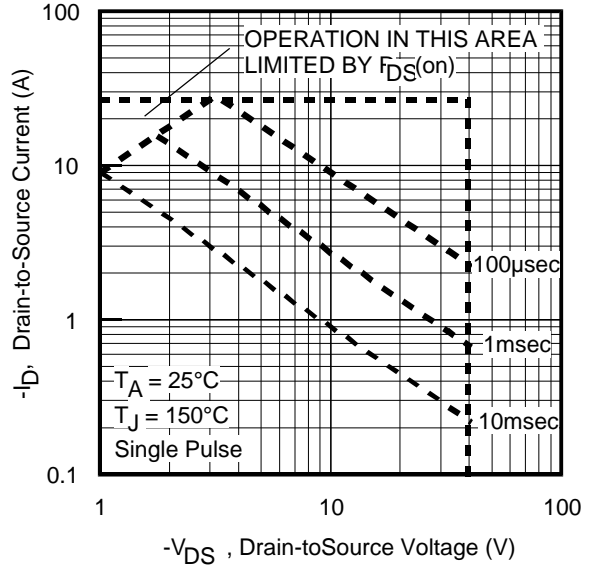
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



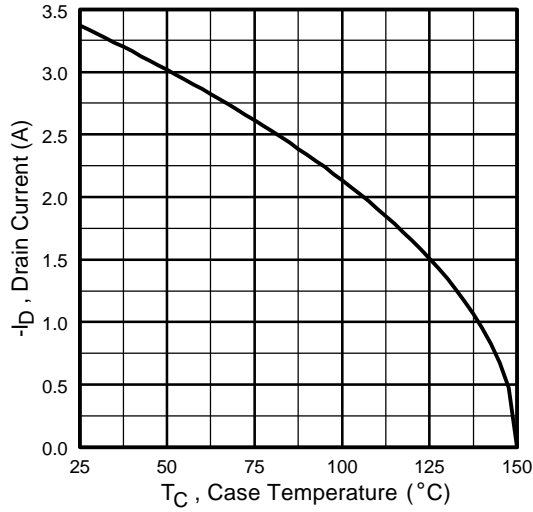
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



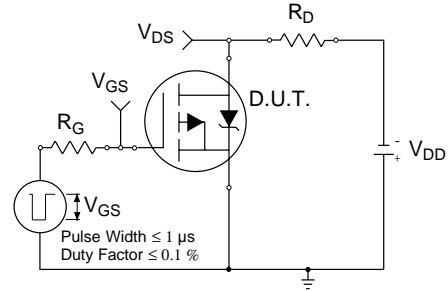
**Fig 7.** Typical Source-Drain Diode Forward Voltage



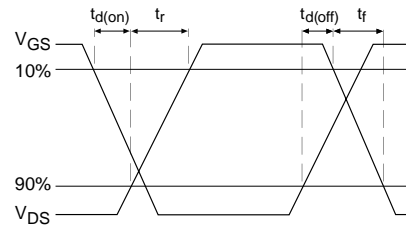
**Fig 8.** Maximum Safe Operating Area



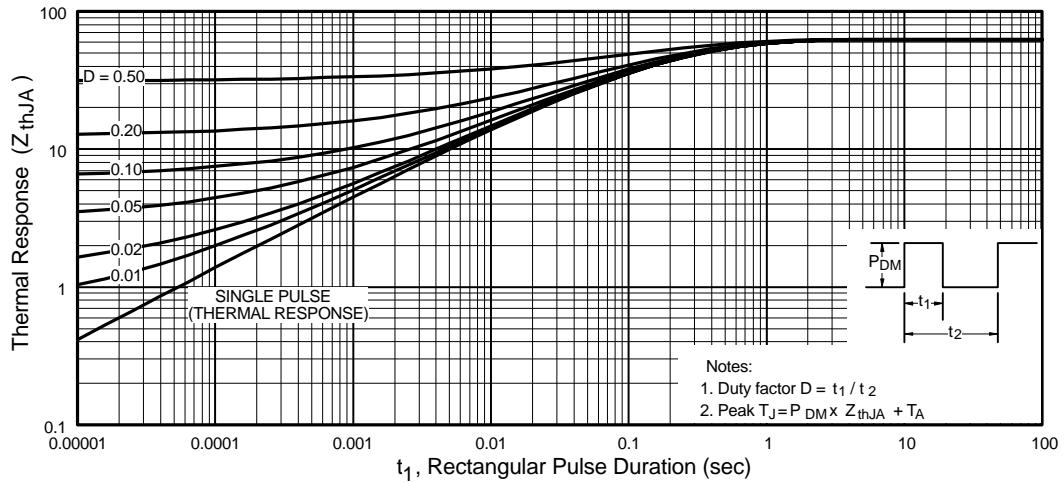
**Fig 9.** Maximum Drain Current Vs. Case Temperature



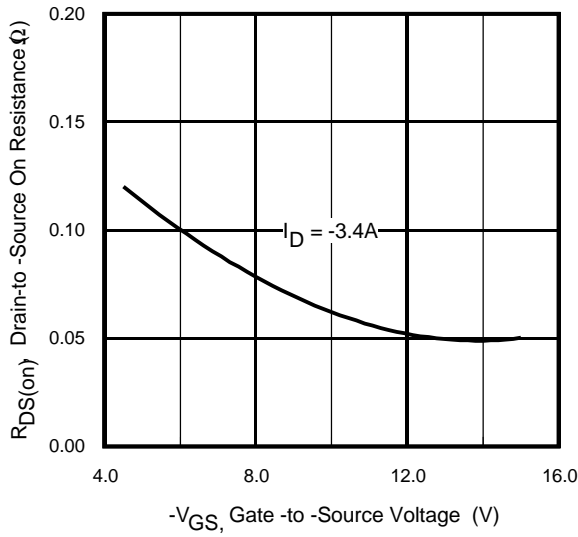
**Fig 10a.** Switching Time Test Circuit



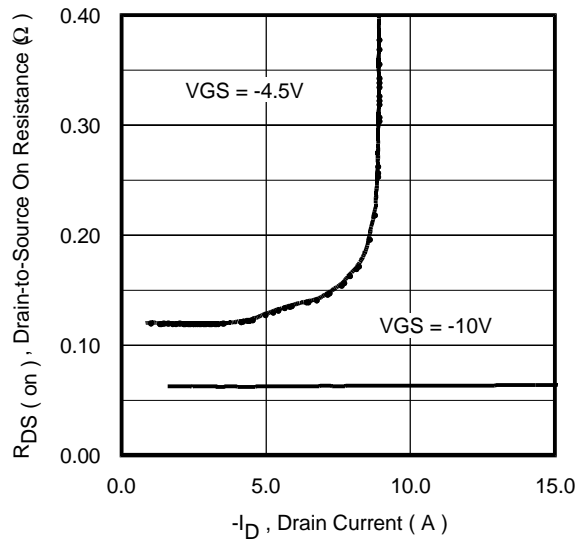
**Fig 10b.** Switching Time Waveforms



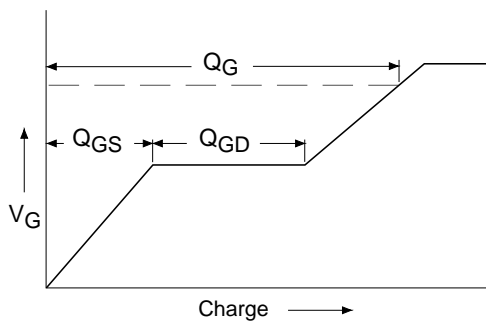
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



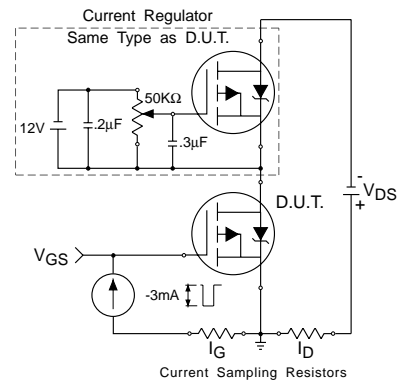
**Fig 12.** Typical On-Resistance Vs. Gate Voltage



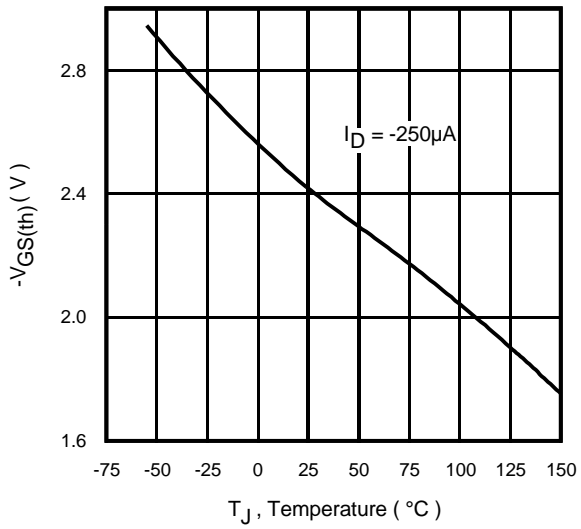
**Fig 13.** Typical On-Resistance Vs. Drain Current



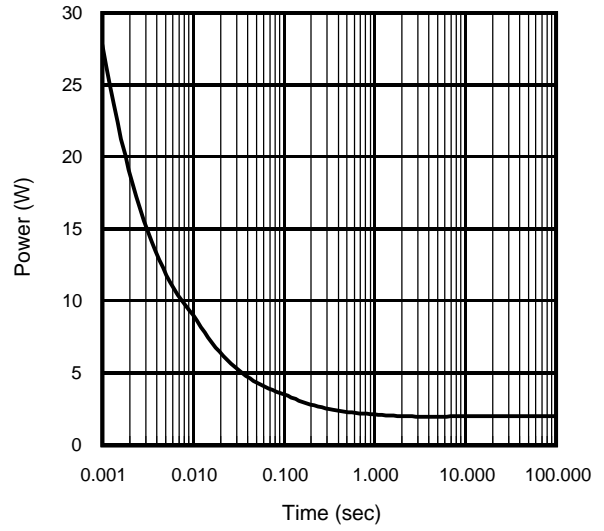
**Fig 14a.** Basic Gate Charge Waveform



**Fig 14b.** Gate Charge Test Circuit



**Fig 15.** Typical Threshold Voltage Vs. Junction Temperature

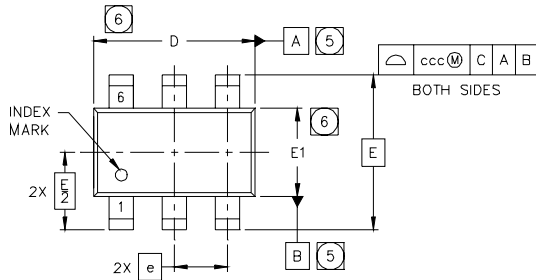


**Fig 16.** Typical Power Vs. Time

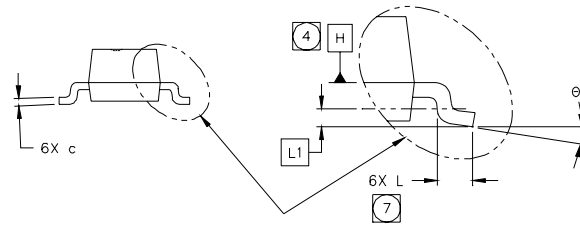
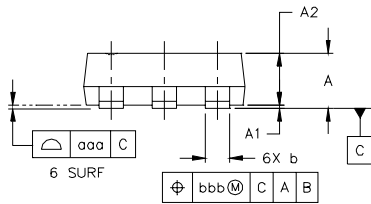
# IRF5803

International  
**IR** Rectifier

## TSOP-6 Package Outline



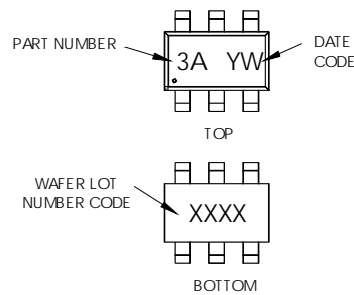
SYMBOL	MO-193AA DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	----	----	.0433
A1	0.01	---	0.10	.0004	---	.0039
A2	0.80	0.90	1.00	.0315	.0354	.0393
b	0.25	---	0.50	.0099	---	.0196
c	0.10	---	0.26	.004	---	.010
D	2.90	3.00	3.10	.115	.118	.122
E	2.75 BSC			.108 BSC		
E1	1.30	1.50	1.70	.052	.059	.066
e	1.00 BSC			.039 BSC		
L	0.20	0.40	0.60	.0079	.0157	.0236
L1	0.30 BSC			.0118 BSC		
θ	0°	---	8°	0°	---	8°
aaa	0.10			.004		
bbb	0.15			.006		
ccc	0.25			.010		



## TSOP-6 Part Marking Information

EXAMPLE: THIS IS AN SI3443DV

WW = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR



YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

PART NUMBER CODE REFERENCE:

- 3A = SI3443DV
- 3B = IRF5800
- 3C = IRF5850
- 3D = IRF5851
- 3E = IRF5852
- 3I = IRF5805
- 3J = IRF5806

DATE CODE EXAMPLES:

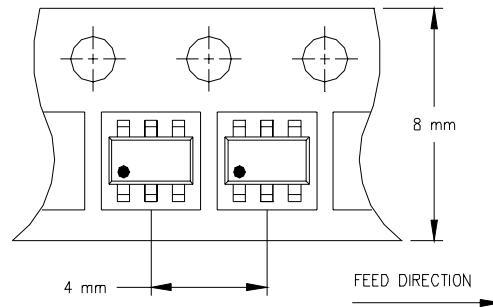
- YWW = 9603 = 6C
- YWW = 9632 = FF

WW = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z

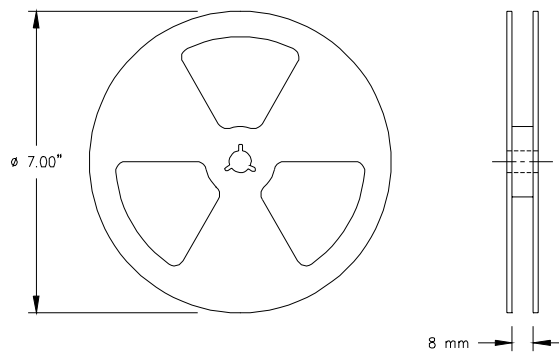


## TSOP-6 Tape & Reel Information



NOTES:

1. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES:

1. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.  
This product has been designed and qualified for the consumer market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

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